

# MC74VHCT50A

## Noninverting Buffer / CMOS Logic Level Shifter with LSTTL-Compatible Inputs

The MC74VHCT50A is a hex noninverting buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

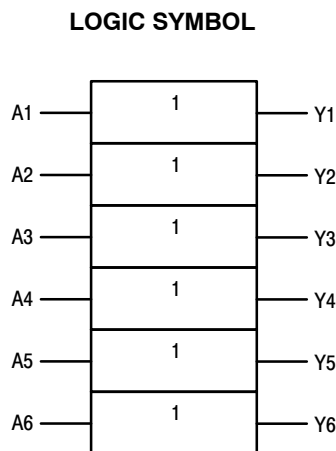
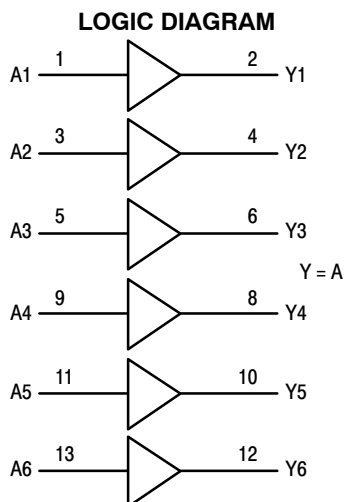
The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHCT50A input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHCT50A to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when  $V_{CC} = 0$  V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

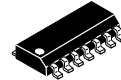
### Features

- High Speed:  $t_{PD} = 3.5$  ns (Typ) at  $V_{CC} = 5$  V
- Low Power Dissipation:  $I_{CC} = 2$   $\mu$ A (Max) at  $T_A = 25^\circ$ C
- TTL-Compatible Inputs:  $V_{IL} = 0.8$  V;  $V_{IH} = 2.0$  V
- CMOS-Compatible Outputs:  $V_{OH} > 0.8 V_{CC}$ ;  $V_{OL} < 0.1 V_{CC}$  @Load
- Power Down Protection Provided on Inputs and Outputs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

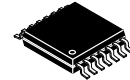


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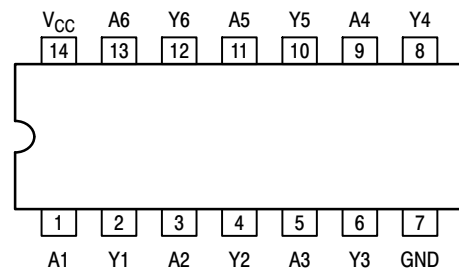


**14-LEAD SOIC  
D SUFFIX  
CASE 751A**



**14-LEAD TSSOP  
DT SUFFIX  
CASE 948G**

### PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

### FUNCTION TABLE

A Input	Y Output
L	L
H	H

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# MC74VHCT50A

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage	- 0.5 to +7.0	V
$V_{IN}$	DC Input Voltage	- 0.5 $\leq V_I \leq$ +7.0	V
$V_{OUT}$	DC Output Voltage Output in HIGH or LOW State	- 0.5 $\leq V_O \leq$ +7.0	V
$I_{IK}$	DC Input Diode Current	- 20	mA
$I_{OK}$	DC Output Diode Current	$\pm$ 20	mA
$I_O$	DC Output Source/Sink Current	$\pm$ 25	mA
$I_{CC}$	DC Supply Current per Supply Pin	$\pm$ 50	mA
$I_{GND}$	DC Ground Current per Ground Pin	$\pm$ 50	mA
$T_{STG}$	Storage Temperature Range	- 65 to + 150	$^{\circ}$ C
$T_L$	Lead Temperature, 1 mm from Case for 10 Seconds	260	$^{\circ}$ C
$T_J$	Junction Temperature under Bias	+ 150	$^{\circ}$ C
$\theta_{JA}$	Thermal Resistance (Note 1) SOIC TSSOP	125 170	$^{\circ}$ C/W
$P_D$	Power Dissipation in Still Air SOIC TSSOP	500 450	mW
$V_{ESD}$	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 2000	V
$I_{Latch-Up}$	Latch-Up Performance Above $V_{CC}$ and Below GND at 85 $^{\circ}$ C (Note 5)	$\pm$ 300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
2. Tested to EIA/JESD22-A114-A.
3. Tested to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.
5. Tested to EIA/JESD78.

## RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	$V_{CC}$	2.0	5.5	V
DC Input Voltage	$V_{IN}$	0.0	5.5	V
DC Output Voltage $V_{CC} = 0$ High or Low State	$V_{OUT}$	0.0 0.0	5.5 $V_{CC}$	V
Operating Temperature Range	$T_A$	-55	+125	$^{\circ}$ C
Input Rise and Fall Time $V_{CC} = 3.3 V \pm 0.3 V$ $V_{CC} = 5.0 V \pm 0.5 V$	$t_r, t_f$	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

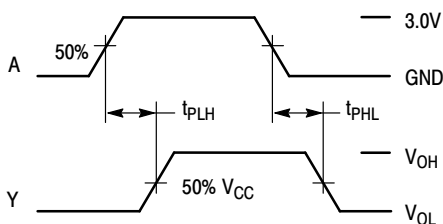
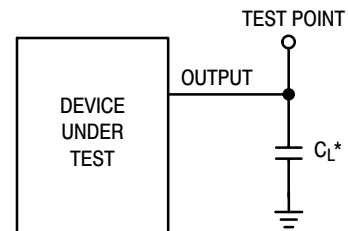


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

# MC74VHCT50A

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			T <sub>A</sub> ≤ 85°C		T <sub>A</sub> ≤ 125°C		Unit	
				Min	Typ	Max	Min	Max	Min	Max		
V <sub>IH</sub>	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V	
V <sub>IL</sub>	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8		V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V	
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -4 mA I <sub>OH</sub> = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V	
V <sub>OL</sub>	Maximum Low-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 50 μA	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1		V
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -4 mA I <sub>OL</sub> = 8 mA	3.0 4.5				0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0		μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			2.0		20		40		μA
I <sub>CC(T)</sub>	Quiescent Supply Current	Input: V <sub>IN</sub> = 3.4 V	5.5			1.35		1.50		1.65		mA
I <sub>OFF</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0.0			0.5		5.0		10		μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS (C<sub>load</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> ≤ 85°C		T <sub>A</sub> ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Y	V <sub>CC</sub> = 3.3 ± 0.3 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0			ns
		V <sub>CC</sub> = 5.0 ± 0.5 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		6.2 7.0	7.5 8.5		8.5 9.5		9.5 10.5	
C <sub>IN</sub>	Maximum Input Capacitance			5 10			10		10	pF

C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)	Typical @ 25°C, V <sub>CC</sub> = 5.0 V		pF
		15		

6. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## NOISE CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns, C<sub>L</sub> = 50pF, V<sub>CC</sub> = 5.0V)

Symbol	Characteristic	T <sub>A</sub> = 25°C		Unit
		Typ	Max	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.8	1.0	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.8	-1.0	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

# MC74VHCT50A

## ORDERING INFORMATION

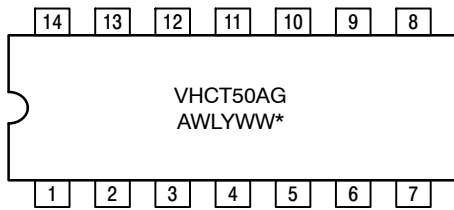
Device	Package	Shipping†
MC74VHCT50ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT50ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLVVHCT50ADTR2G*		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

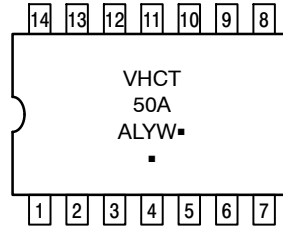
\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

## MARKING DIAGRAMS

(Top View)



**14-LEAD SOIC  
D SUFFIX  
CASE 751A**



**14-LEAD TSSOP  
DT SUFFIX  
CASE 948G**

A = Assembly Location  
 WL, L = Wafer Lot  
 Y = Year  
 WW, W = Work Week  
 G or ▪ = Pb-Free Package

\*See Applications Note #AND8004/D for date code and traceability information.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

SOIC-14 NB  
CASE 751A-03  
ISSUE L

DATE 03 FEB 2016



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
  5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

### SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### GENERIC MARKING DIAGRAM\*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

### STYLES ON PAGE 2

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**SOIC-14**  
**CASE 751A-03**  
**ISSUE L**

DATE 03 FEB 2016

STYLE 1:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. NO CONNECTION  
 5. ANODE/CATHODE  
 6. NO CONNECTION  
 7. ANODE/CATHODE  
 8. ANODE/CATHODE  
 9. ANODE/CATHODE  
 10. NO CONNECTION  
 11. ANODE/CATHODE  
 12. ANODE/CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 2:  
 CANCELLED

STYLE 3:  
 PIN 1. NO CONNECTION  
 2. ANODE  
 3. ANODE  
 4. NO CONNECTION  
 5. ANODE  
 6. NO CONNECTION  
 7. ANODE  
 8. ANODE  
 9. ANODE  
 10. NO CONNECTION  
 11. ANODE  
 12. ANODE  
 13. NO CONNECTION  
 14. COMMON CATHODE

STYLE 4:  
 PIN 1. NO CONNECTION  
 2. CATHODE  
 3. CATHODE  
 4. NO CONNECTION  
 5. CATHODE  
 6. NO CONNECTION  
 7. CATHODE  
 8. CATHODE  
 9. CATHODE  
 10. NO CONNECTION  
 11. CATHODE  
 12. CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 5:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. ANODE/CATHODE  
 5. ANODE/CATHODE  
 6. NO CONNECTION  
 7. COMMON ANODE  
 8. COMMON CATHODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. ANODE/CATHODE  
 12. ANODE/CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 6:  
 PIN 1. CATHODE  
 2. CATHODE  
 3. CATHODE  
 4. CATHODE  
 5. CATHODE  
 6. CATHODE  
 7. CATHODE  
 8. ANODE  
 9. ANODE  
 10. ANODE  
 11. ANODE  
 12. ANODE  
 13. ANODE  
 14. ANODE

STYLE 7:  
 PIN 1. ANODE/CATHODE  
 2. COMMON ANODE  
 3. COMMON CATHODE  
 4. ANODE/CATHODE  
 5. ANODE/CATHODE  
 6. ANODE/CATHODE  
 7. ANODE/CATHODE  
 8. ANODE/CATHODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. COMMON CATHODE  
 12. COMMON ANODE  
 13. ANODE/CATHODE  
 14. ANODE/CATHODE

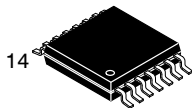
STYLE 8:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. NO CONNECTION  
 5. ANODE/CATHODE  
 6. ANODE/CATHODE  
 7. COMMON ANODE  
 8. COMMON ANODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. NO CONNECTION  
 12. ANODE/CATHODE  
 13. ANODE/CATHODE  
 14. COMMON CATHODE

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 2:1

TSSOP-14 WB  
CASE 948G  
ISSUE C

DATE 17 FEB 2016



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

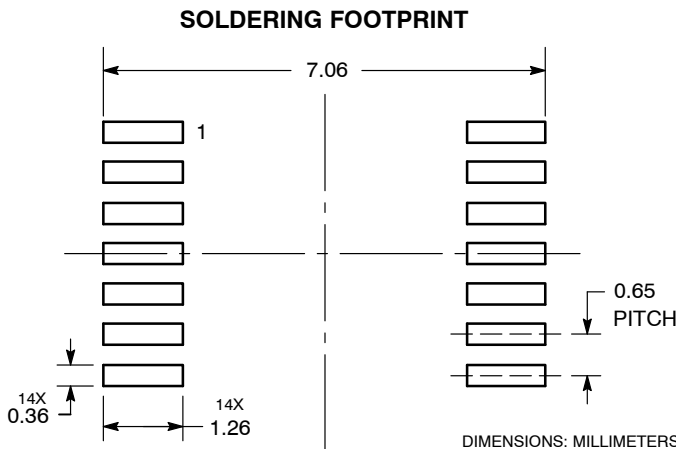
GENERIC MARKING DIAGRAM\*



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.



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